



EXPRESS MAIL NO. EV170139874US

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Present Application:

Applicant : Paolo Menegoli  
Title : DMOS TRANSISTORS WITH SCHOTTKY  
DIODE BODY STRUCTURE  
Docket No. : 96-S-119D2 (850063:498C1)  
Date : September 27, 2002

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Box RCE  
Commissioner for Patents  
Washington, DC 20231

PRELIMINARY AMENDMENT

Commissioner for Patents:

Applicant respectfully requests that the above-identified application be amended as follows:

In the Claims:

Please amend claim 17, and add new claims 21-25 to read as follows:

17. (Twice Amended) A method of operating a [vertical DMOS] transistor in an integrated circuit, the transistor having a drain of first conductivity formed in a buried region of same conductivity, a body formed of second conductivity in an epitaxial layer of first conductivity to form a pn junction diode with the drain, a source of first conductivity in the body, a gate electrode positioned above the source, the body, and the epitaxial layer, a conductive contact coupled to the drain, and a metallic source contact coupled to the source and to the